

140V PNP HIGH-VOLTAGE TRANSISTOR IN SOT89

Features

- BVcEo > -140V
- Ic = -3A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -75mV @ -0.5A
- R_{sat} = 85mΩ for a Low Equivalent On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (ZXTP2014ZQ)

Mechanical Data

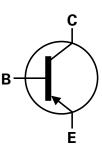
- Package: SOT89
- Package Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>®
- Weight: 0.05 grams (Approximate)

Application

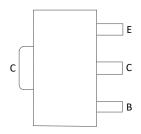
- Motor driving
- Line switching
- · High-side switches
- Subscriber line interference cards (SLIC)







Device Symbol



Top View Pinout

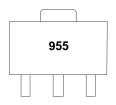
Ordering Information (Note 4)

Orderable Part Number	Dookogo	Marking	Reel Size (inches)	Tana Width (mm)	Packing	
Orderable Part Number	Package Marking Reel Size (inches	Reel Size (Illiches)	Tape Width (mm)	Qty.	Carrier	
ZXTP2014ZTA	SOT89	955	7	12	1,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



955 = Product Type Marking Code



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	-180	V
Collector-Emitter Voltage	V _{CEO}	-140	V
Emitter-Base Voltage	VEBO	-7	V
Continuous Collector Current	lc	-3	Α
Peak Pulse Current	Ісм	-10	Α

Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	PD	1.5 12	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	PD	2.1 16.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	D	83	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	60	°C/W
Thermal Resistance, Junction to Case (Note 5)	Rejc	18.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

 ^{5.} For a device surface-mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single-sided 1oz copper, in still air conditions; device measured when operating in steady-state condition.
 6. Same as Note 5, except the device is mounted on 50mm x 1.6mm single-sided 1oz weight copper.



Thermal Characteristics and Derating Information

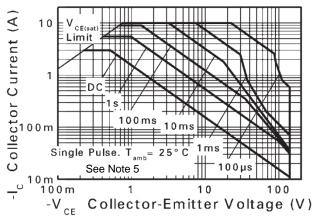


Figure 1. Safe Operating Area

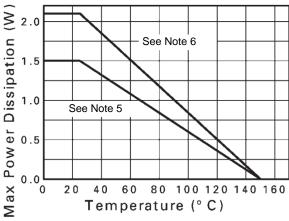


Figure 2. Derating Curve

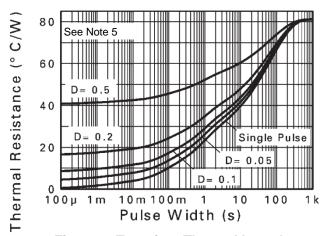


Figure 3. Transient Thermal Impedance

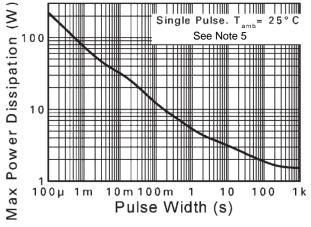


Figure 4. Pulse Power Dissipation



Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	-180	-200	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BVcer	-180	-200	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector- Emitter Breakdown Voltage (Note 7)	BVceo	-140	-160	_	V	IE = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-7.0	-8.0	_	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	_	-1 —	-20 -0.5	nΑ μΑ	V _{CB} = -150V V _{CB} = -150V, T _A = +100°C
Collector-Emitter Cutoff Current	ICER	_	-1 —	-20 -0.5	nΑ μΑ	V_{CB} = -150V, R \leq 1k Ω V_{CB} = -150V, T _A = +100°C, R \leq 1k Ω
Emitter Cutoff Current	I _{EBO}	_	-1	-10	nA	V _{EB} = -6V
Collector-Emitter Saturation Voltage (Note 7)	VCE(sat)	_	-37 -50 -80 -255	-60 -75 -115 -330	mV	I _C = -0.1A, I _B = -5mA I _C = -0.5A, I _B = -50mA I _C = -1A, I _B = -100mA I _C = -3A, I _B = -300mA
Base-Emitter Saturation Voltage (Note 7)	V _{BE(sat)}	_	-970	-1010	mV	$I_C = -3A$, $I_B = -300mA$
Base-Emitter Turn-On Voltage (Note 7)	V _{BE(on)}	_	-800	-900	mV	Ic = -3A, VcE = -5V
Static Forward Current Transfer Ratio (Note 7)	hFE	100 100 45 —	255 200 100 5	300 — —	_	I _C = -10mA, V _{CE} = -5V I _C = -1A, V _{CE} = -5V I _C = -3A, V _{CE} = -5V I _C = -10A, V _{CE} = -5V
Transitional Frequency	f⊤	_	120	_	MHz	Ic = -100mA, VcE = -10V, f = 50MHz
Output Capacitance	C _{obo}	_	33	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	ton	42			ns	Ic = -1A, Vcc = -50V,
Switching Tillle	t _{off}		636	_	115	$I_B1 = -I_B2 = -100 \text{mA}$

Note:

7. Measured under pulsed conditions. Pulse width \leq 300 $\mu s.$ Duty cycle \leq 2%.



Typical Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)

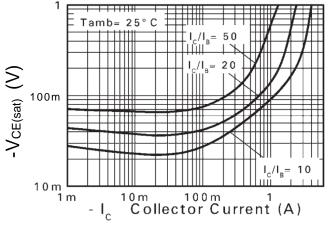


Figure 5. V_{CE(sat)} vs. I_C

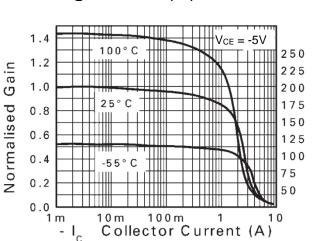
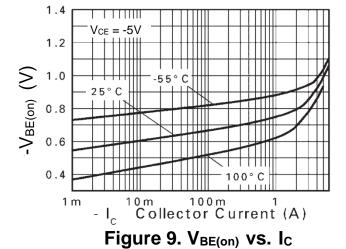


Figure 7. hFE vs. Ic



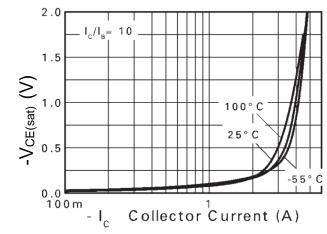


Figure 6. V_{CE(sat)} vs. I_C

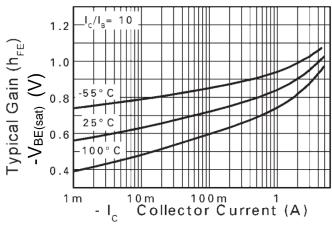


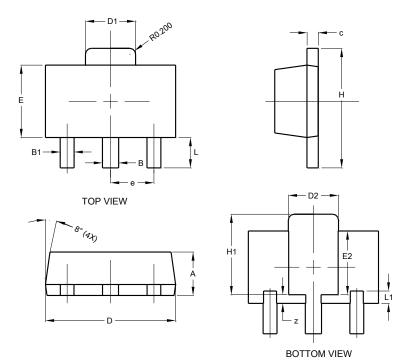
Figure 8. V_{BE(sat)} vs. I_C



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

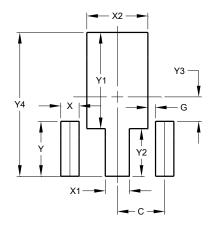


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
C	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	1	-	1.50		
Η	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
١	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)
С	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530



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